

	No.4747	2SJ267 P-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Surface mount type device making the following possible
 - Reduction in the assembling time for 2SJ267-applied equipment
 - High-density surface mount applications
 - Small size of 2SJ267-applied equipment

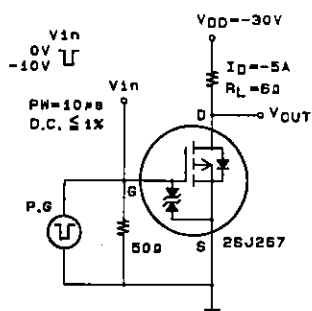
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Drain-to-Source Voltage	V_{DS}	-60	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Drain Current(DC)	I_D	-10	A
Drain Current(Pulse)	I_{DP}	-40	A
Allowable Power Dissipation	P_D	1.65	W
		$T_c = 25^\circ\text{C}$	
		60	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

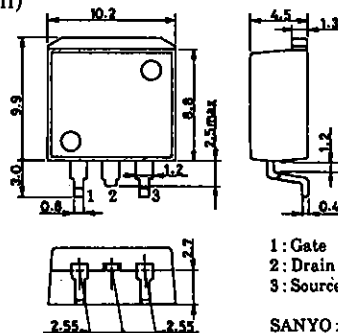
Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}, V_{GS} = 0$	-60			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu\text{A}, V_{DS} = 0$	± 20			V
Zero-Gate Voltage	I_{DSS}	$V_{DS} = -60\text{V}, V_{GS} = 0$			-100	μA
Drain Current						
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16\text{V}, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}, I_D = -1\text{mA}$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10\text{V}, I_D = -5\text{A}$	4	7.5		S
Static Drain-to-Source	$R_{DS(on)}$	$I_D = -5\text{A}, V_{GS} = -10\text{V}$		0.11	0.15	Ω
ON-State Resistance	$R_{DS(on)}$	$I_D = -5\text{A}, V_{GS} = -4\text{V}$		0.15	0.2	Ω
Input Capacitance	C_{iss}	$V_{DS} = -20\text{V}, f = 1\text{MHz}$		1230		pF
Output Capacitance	C_{oss}	$V_{DS} = -20\text{V}, f = 1\text{MHz}$		390		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20\text{V}, f = 1\text{MHz}$		100		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		16		ns
Rise Time	t_r	"		40		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		230		ns
Fall Time	t_f	"		150		ns
Diode Forward Voltage	V_{SD}	$I_S = -10\text{A}, V_{GS} = 0$	-1.0	-1.5		V

Switching Time Test Circuit

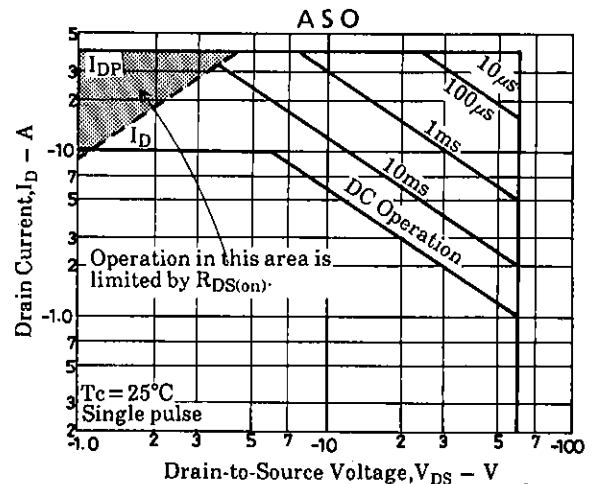
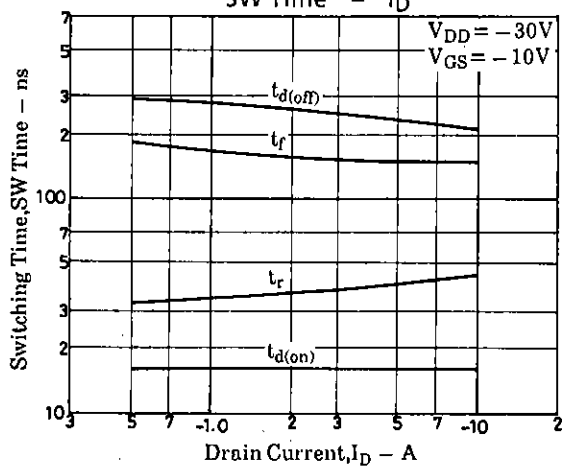
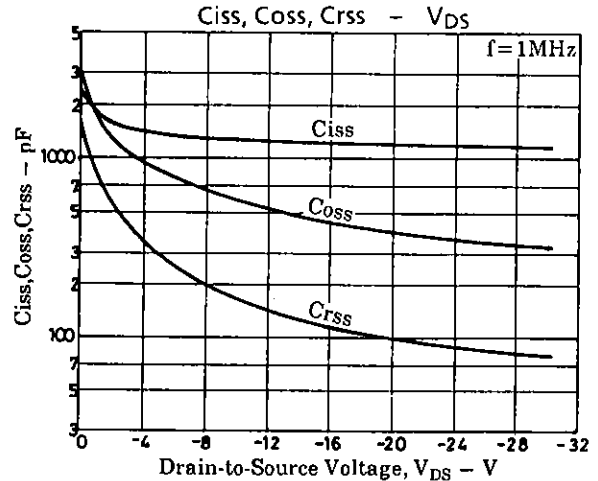
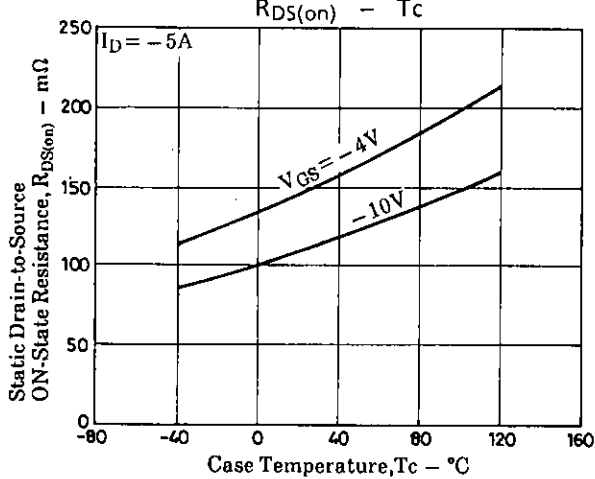
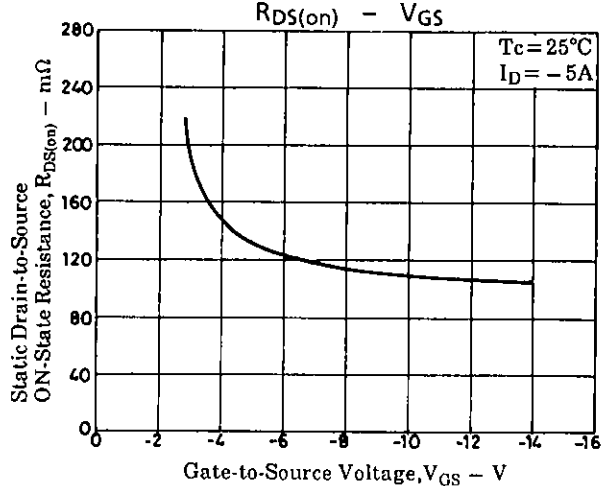
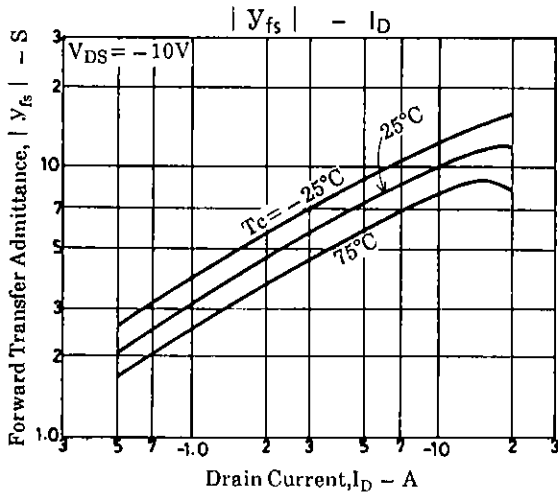
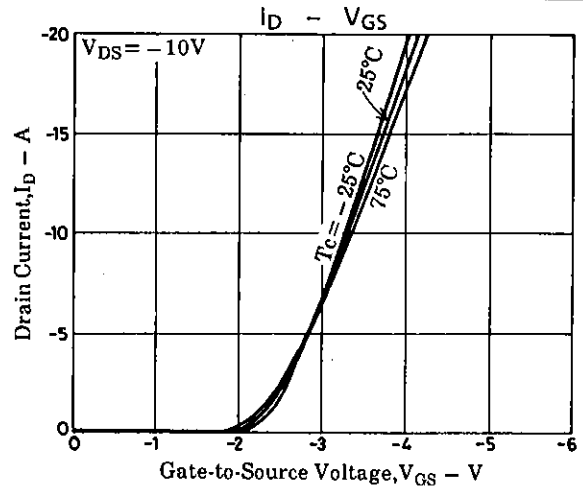
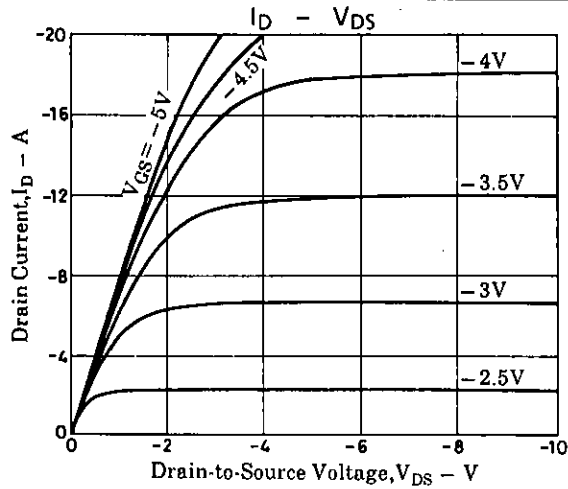


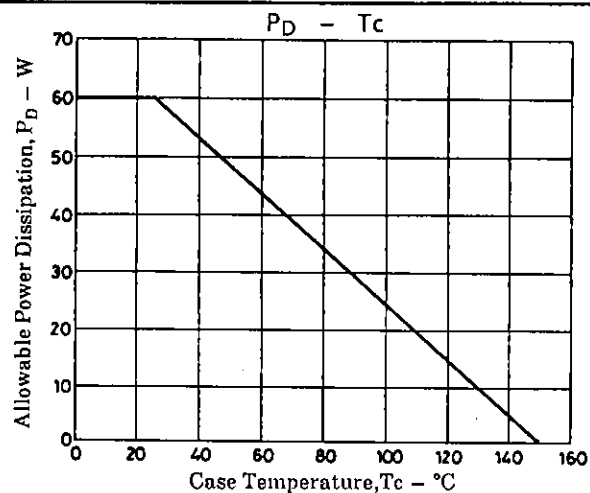
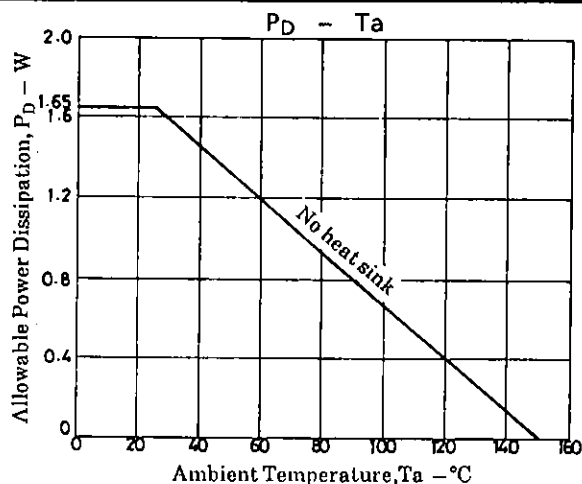
Package Dimensions 2090A (unit : mm)


1: Gate
2: Drain
3: Source

SANYO: SMP-FD

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